

Form PTO-1449 (Modified)	Atty Docket No. 2616 US/RTP/LE	Serial No.
<i>List of Patents & Publications Statement</i>	Applicant(s): Xing, Miner, Lopes, Kaluri & Tauber	
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U.S. PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Name	Class	Sub-class	Filing Date (if appropriate)
	AA						
	AB						
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FOREIGN PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Country	Class	Sub-class	Translation Yes	No
	AH							
	AI							
	AJ							
	AK							

OTHER ART (Including Title, Author, Date, Pertinent Pages, etc.)

Exam. Initials		Document Identification
	AL	Hattangady, S.V.; Niimi, H.; & Lucovsky, G., "Controlled nitrogen incorporation at the gate oxide surface," Appl. Phys. Lett. Vol. 66, No. 25, June 19, 1995, pp. 3495-3497.
	AM	Kaluri, S.R. & Hess, D.W., "Nitrogen incorporation in thin oxides by constant current N ₂ O plasma anodization of silicon and N ₂ plasma nitridation of silicon oxide," Appl. Phys. Lett., Vol. 69, No. 8, August 19, 1996, pp. 1053-1055.
	AN	Kaluri, S.R. & Hess, D.W., "Constant Current N ₂ O Plasma Anodization of Silicon," J. Electrochem. Soc., Vol. 144, No. 6, June 1997, pp. 2200-2205.
	AO	Kraft, R.; Schneider, T.P.; Dostalík, W.W.; & Hattangady, S., "Surface nitridation of silicon dioxide with a high density nitrogen plasma," J. Vac. Sci. Technol. B, Vol. 15, No. 4, Jul/Aug 1997, pp. 967-970.
	AP	

Examiner: *Paul J. Jorgensen*

Date Considered: *November 14, 2000*

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.